



M8050

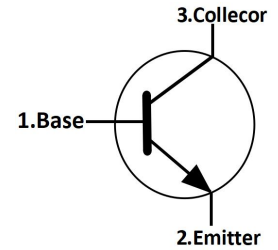
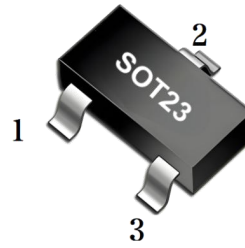
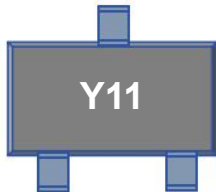
NPN SILICON TRANSISTOR

FEATURES

*Power dissipation

MARKING

Type Code: Marking: Y11



ABSOLUTE MAXIMUM RATINGS (Tc=25°C, unless otherwise specified)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|---|---------|------|
| V _{CB0} | Collector-base voltage | 40 | V |
| V _{CEO} | Collector-emitter voltage | 25 | V |
| V _{EBO} | Emitter-base voltage | 6 | V |
| I _c | Collector current | 0.8 | A |
| P _c | Collector Power Dissipation | 200 | mW |
| T _j | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -55~150 | °C |
| ROJA | Thermal Resistance From Junction To Ambient | 625 | °C/W |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

ELECTRICAL CHARACTERISTICS (Tc=25°C, unless otherwise specified)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | MAX | UNIT |
|--|------------------------|---|-----|-----|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =100μA, I _E =0 | 40 | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO} * | I _C =1mA, I _B =0 | 25 | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =100μA, I _C =0 | 6 | | V |
| Collector cutoff current | I _{CB0} | V _{CB} =35V, I _E =0 | | 0.1 | μA |
| Collector cut-off current | I _{CEO} | V _{CE} =20V, I _B =0 | | 0.1 | μA |
| DC Current Gain (CLASSIFICATION OF h _{FE2}) | h _{FE1} | V _{CE} =1V, I _C =5mA | 45 | | |
| | h _{FE2} | V _{CE} =1V, I _C =100mA | A | 80 | 300 |
| | | | B | 300 | 400 |
| | H _{FE3} | V _{CE} =1V, I _C =800mA | 40 | | |
| Collector-emitter saturation voltage | V _{CE(sat)} | I _C =800mA, I _B =80mA | | 0.5 | V |
| Base-Emitter Saturation Voltage | V _{BE(sat)} | I _C =800mA, I _B =80mA | | 1.2 | V |
| Transition frequency | f _T | V _{CE} =6V, I _C = 20mA, f=30MHz | 150 | | MHz |

*Note:Pulse test: Pulse Width <300μs, Duty Cycle<2%.

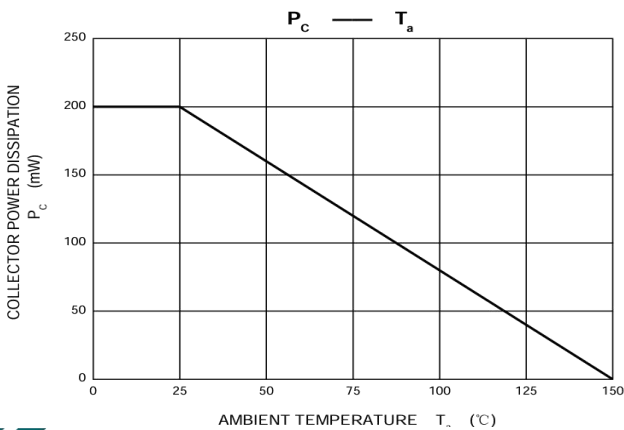
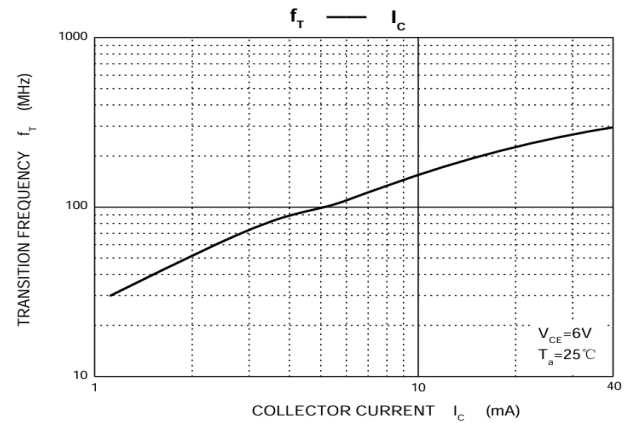
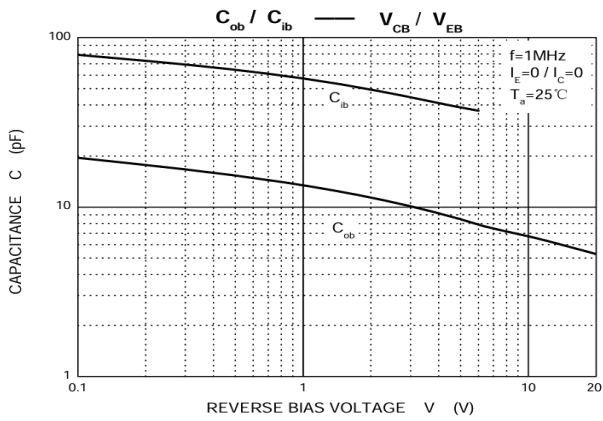
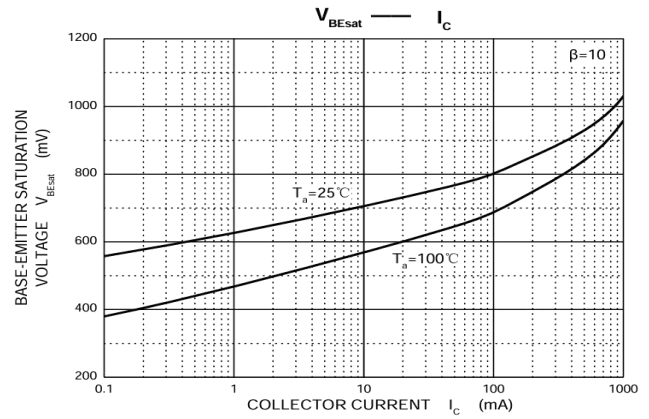
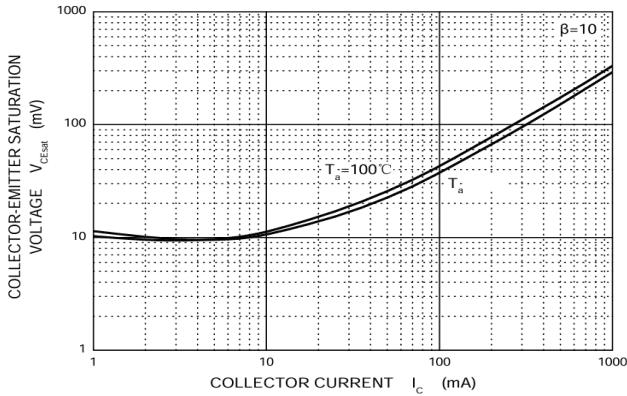
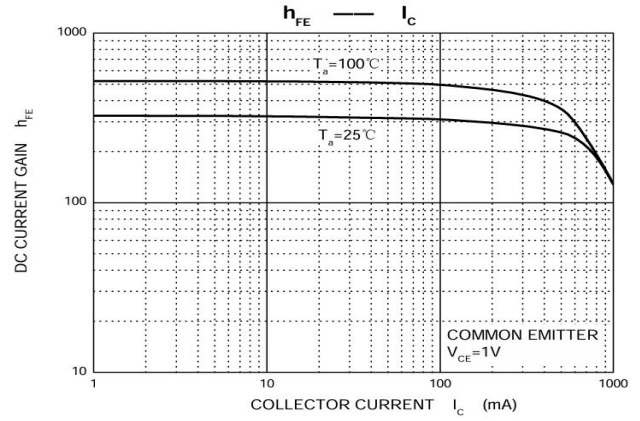
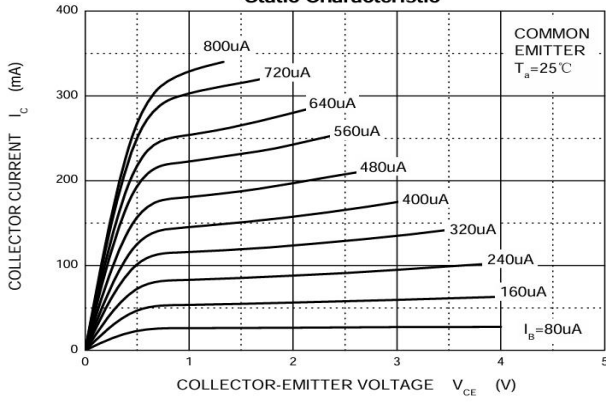


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■ TYPICAL CHARACTERISTICS

Static Characteristic

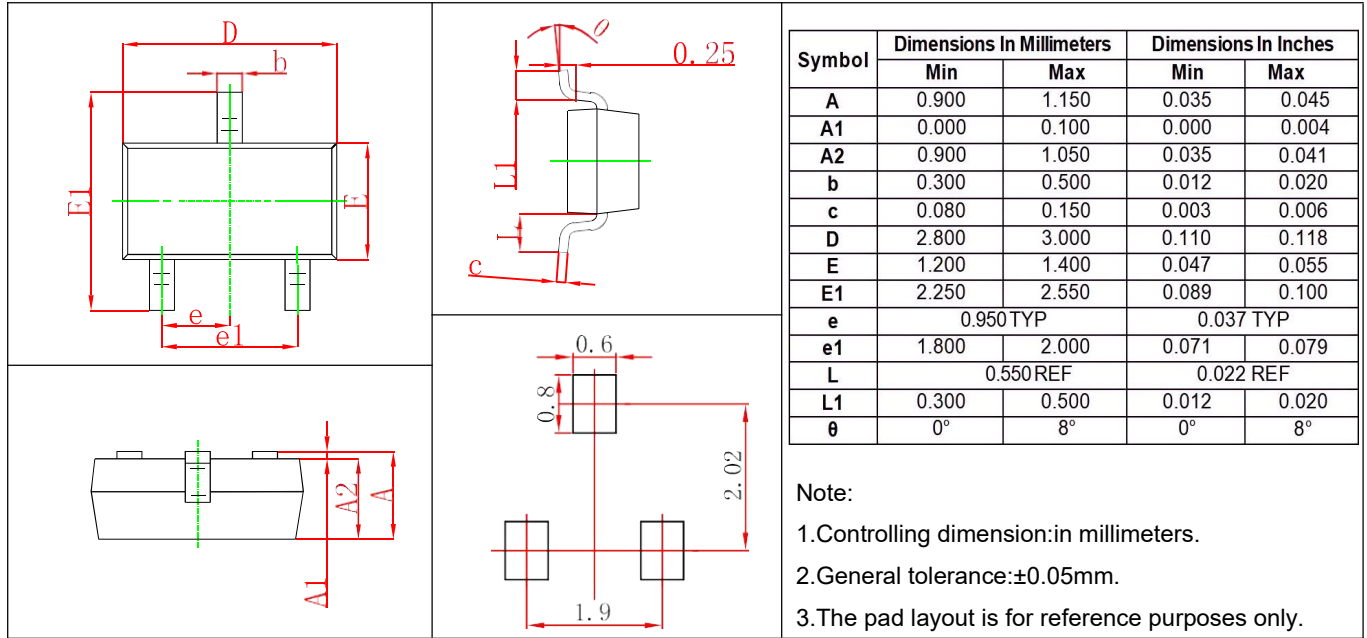




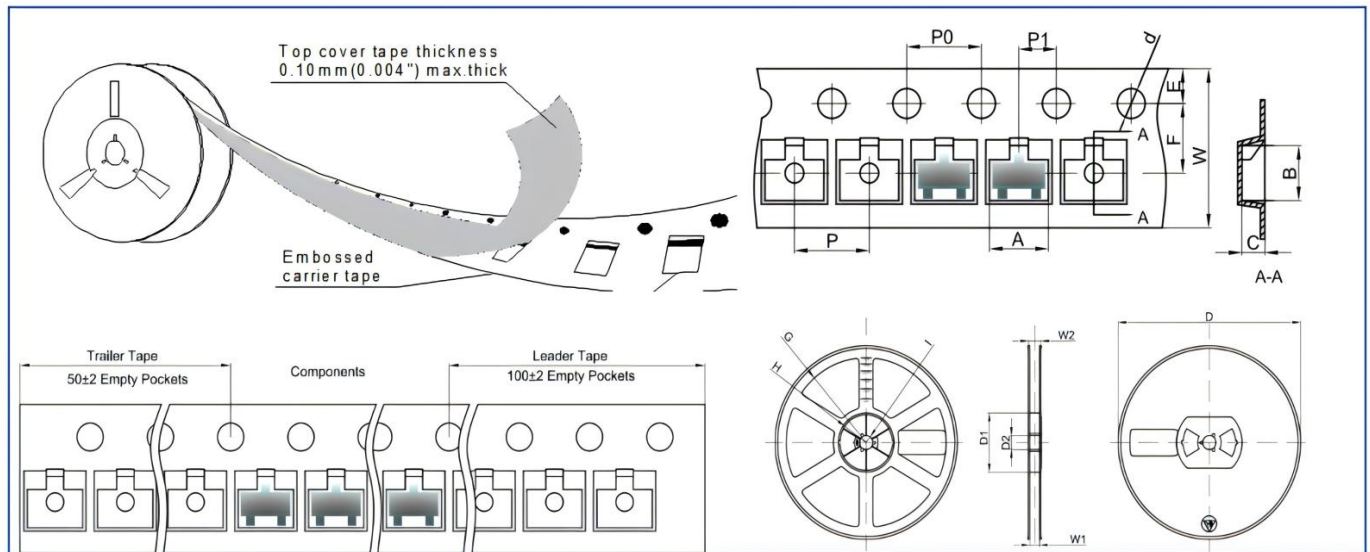
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NPN SILICON TRANSISTOR

■ SOT23 PACKAGE OUTLINE DIMENSIONS



■ REEL PACKING



| Dimensions are in millimeter | | | | | | | | | | |
|------------------------------|--------|-------|-------|--------|--------|-------|------|-------|---------------|------|
| PKG TYPE | A | B | C | d | E | F | Po | P | P1 | W |
| SOT-23 | 3.15 | 2.77 | 1.22 | Φ1.50 | 1.75 | 3.50 | 4.00 | 4.00 | 2.00 | 8.00 |
| Reel Optiom | D | D1 | D2 | G | H | I | W1 | W2 | Q.TY PER REEL | |
| 7" Dia | Φ178.0 | 54.40 | 13.00 | R78.00 | R25.60 | R6.50 | 9.50 | 12.30 | 3000PCS | |
| 13" Dia | φ330.0 | / | 13.00 | / | / | R6.50 | 9.50 | 12.30 | 10000PCS | |